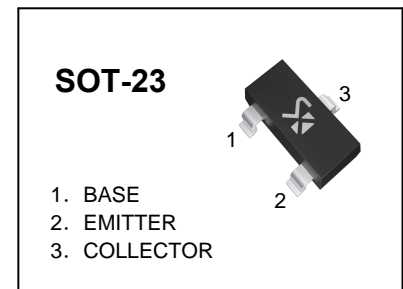


PNP Silicon Epitaxial Planar Transistor

For switching and amplifier applications.
Especially suitable for AF-driver stages and
low power output stages.



MARKING: 2TY

MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CB0}	Collector-Base Voltage	-50	V
V_{CE0}	Collector-Emitter Voltage	-30	V
V_{EB0}	Emitter-Base Voltage	-8	V
I_C	Collector Current -Continuous	-500	mA
P_C	Collector Power Dissipation	300	mW
T_j	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55-150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CB0}$	$I_C = -0.05\text{mA}, I_E = 0$	-50			V
Collector-emitter breakdown voltage	$V_{(BR)CE0}$	$I_C = -1\text{mA}, I_B = 0$	-30			V
Emitter-base breakdown voltage	$V_{(BR)EB0}$	$I_E = -0.05\text{mA}, I_C = 0$	-8			V
Collector cut-off current	I_{CB0}	$V_{CB} = -35\text{V}, I_E = 0$			-0.1	μA
Emitter cut-off current	I_{EB0}	$V_{EB} = -4\text{V}, I_C = 0$			-0.1	μA
DC current gain	h_{FE}	$V_{CE} = -1\text{V}, I_C = -50\text{mA}$	85		400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -500\text{mA}, I_B = -50\text{mA}$			-0.6	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -500\text{mA}, I_B = -50\text{mA}$			-1.2	V
Transition frequency	f_T	$V_{CE} = -6\text{V}, I_C = -20\text{mA}$ $f = 30\text{MHz}$	150			MHz

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT-23

